

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Patent Application of	:	Confirmation No.: 8389
Thierry Duffar	:	Group Art Unit: 1792
	:	
Serial No. 10/587,368	:	Atty. Dkt: Beaumont - 39
	:	
Filing Date: 05/07/2007	:	Examiner: HITESHEW, FELISA CARLA
	:	
For: METHOD AND DEVICE FOR PRODUCING MONOCRYSTALS		
Date: October 6, 2008		

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INTERVIEW SUMMARY PURSUANT TO 37 CFR 1.133

A telephonic interview was conducted on October 6, 2008 between Applicant's representative Mitesh Mehta, Reg. No. L0349 and Primary Examiner Felisa Carla Hiteshew. The discussion centered on proposed amendments to Claims 1 and 3.

The parties discussed the subject matter of claims 1 and 3 relative to the Iwasaki (JP 62227569) reference. An agreement was reached as to Claim 1, wherein terms "responsive to alternating current signal," would be included after the phrase "electromagnetic field generation means" on line 9. It was submitted to the Examiner that the support for this amendment is found at Page 6, lines 6 – 24 of the Specification, by way of non-limiting example only. It was further agreed that the cited art of record, singularly or in combination, fails to teach each of the features and limitations of proposed Claim 1.

As to Claim 3, the phrase "forming and maintaining a meniscus at the interface of the solid and the liquid phase by" would be included immediately before the phrase "simultaneously applying ..." on line 8. It was submitted to the Examiner that the support for this amendment is found at Page 7, lines 5 – 8 and lines 29 – 30 of the Specification, by way of non-limiting example only. It was further agreed that the cited art of record, singularly or in combination, fails to teach each of the features and limitations of proposed Claim 3.

It was further agreed upon that the Examiner would amend Claims 1 and 3 via an Examiner's Amendment and that a Supplemental Notice of Allowability shall be forthcoming. The Examiner further indicated that she will prepare an Interview Summary. Applicants reserve their right to comment on the same upon the receipt of the Interview Summary from the Examiner.

Respectfully submitted,



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Dated: OCTOBER 6, 2008

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PROPOSED CLAIM AMENDMENTS
FOR DISCUSSION PURPOSES ONLY

1. (Proposed Amendment) A device for manufacturing a single-crystal solid phase by solidification of a liquid phase, comprising:

a crucible capable of containing the solid phase and the liquid phase, the liquid phase being in contact with the crucible and the solid phase being separated from the crucible by an interstice; and

means for heating the liquid phase capable of creating a thermal gradient at the level of an interface between the liquid phase and the solid phase,

electromagnetic field generation means, responsive to alternating current signal, distinct from the heating means, for applying an electromagnetic pressure on the junction surface of the liquid phase at the level of said interface

comprising at least one spiral surrounding the crucible, and placed opposite to the area in which said interface forms in operation.

3. (Proposed Amendment) A method for manufacturing a single-crystal solid phase by solidification of a liquid phase comprising the steps of:

providing a crucible containing the solid phase and the liquid phase, the liquid phase being in contact with the crucible, the solid phase being separated from the crucible by an interstice;

applying a thermal gradient at the level of an interface between the liquid phase and the solid phase; and

forming and maintaining a meniscus at the interface between the liquid phase and the solid phase by simultaneously applying an electromagnetic pressure over the entire junction surface of the liquid phase at the level of said interface.